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[Continued on next page]

(54) Title: SURFACE TREATMENT FOR MOLECULAR BONDING

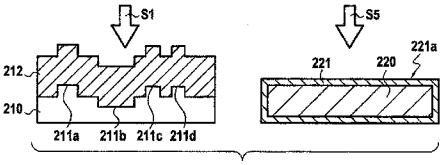

FIG.3B

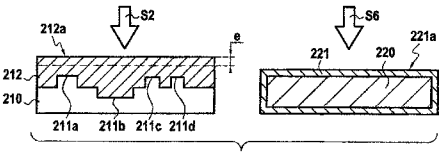

FIG.3C

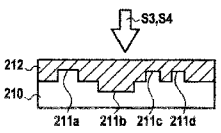

FIG.3D

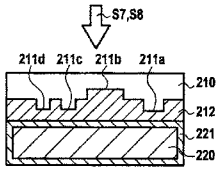

FIG.3E

(57) Abstract: A method of bonding a first substrate (210) on a second substrate (220) by molecular bonding, the method comprising the following steps: • forming a layer of insulation (212) on the bonding face (210a) of the first substrate (210); • chemical -mechanical polishing said layer of insulation (212); • activating the bonding surface of the second substrate (220) by plasma treatment; and • bonding together the two substrates (210, 220) by molecular bonding; the method being characterized in that it further comprises, after the chemical -mechanical polishing step and before the bonding step, a step of etching the surface (212a) of the layer of insulation (212) formed on the first substrate.

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